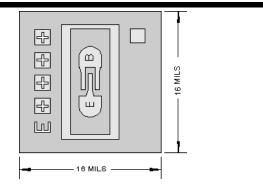


Chip Type 2C918 Geometry 0013 Polarity NPN Data Sheet No. 2C918

## **Generic Packaged Parts:**

**Request Quotation** 

2N918



Chip type **2C918** by Semicoa Semiconductors provides performance similar to these devices.

## Part Numbers:

2N918, 2N918UB, SD918, SD918F, SQ918, SQ918F

## **Product Summary:**

**APPLICATIONS:** Designed for high frequency oscillator, multiplier and driver applications.

## Features:

• High frequency rating

| Mechanical Specifications |                   |                     |  |  |  |
|---------------------------|-------------------|---------------------|--|--|--|
| Metallization             | Тор               | AI - 15 kÅ min.     |  |  |  |
|                           | Backside          | Au - 6.5 kÅ nom.    |  |  |  |
| Bonding Pad Size          | Emitter           | 2.7 mils x 2.7 mils |  |  |  |
|                           | Base              | 2.7 mils x 2.7 mils |  |  |  |
| Die Thickness             | 8 mils nominal    |                     |  |  |  |
| Chip Area                 | 16 mils x 16 mils |                     |  |  |  |
| Top Surface               | Silox Passivated  |                     |  |  |  |

| Electrical Characteristics<br>$T_A = 25^{\circ}C$ |   |     |     |      |  |  |
|---|---|-----|-----|------|--|--|
| Parameter   | Test conditions   | Min | Max | Unit |  |  |
| BV <sub>CEO</sub>                                 | $I_{\rm C} = 3.0 \text{ mA}, I_{\rm B} = 0$                 | 15  |     | V dc |  |  |
| BV <sub>CBO</sub>                                 | $I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$                   | 30  |     | V dc |  |  |
| BV <sub>EBO</sub>                                 | $I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$                   | 3.0 |     | V dc |  |  |
| I <sub>CBO</sub>                                  | $V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0$                  |     | 10  | nA   |  |  |
| h <sub>FE</sub>                                   | $I_{\rm C} = 3.0 \text{ mA dc}, V_{\rm CE} = 1.0 \text{ V}$ | 20  |     |      |  |  |
| V <sub>CE(sat)</sub>                              | $I_{\rm C} = 30 \text{ mA dc}, I_{\rm B} = 3.0 \text{ mA}$  |     | 0.3 | V dc |  |  |

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu$ s, duty cycle less than 2%.